POLISHING COMPOSITION AND METHOD FOR HIGH SILICON NITRIDE TO SILICON OXIDE REMOVAL RATE RATIOS

ABSTRACT

The invention provides a chemical-mechanical polishing composition comprising a cationic abrasive, a cationic polymer, a carboxylic acid, and water. The invention further provides a method of chemically-mechanically polishing a substrate with the aforementioned polishing composition. The polishing composition exhibits selectivity for removal of silicon nitride over removal of silicon oxide.

(No Figure)